Abstracts

Highly Reliable GaAs MESFETs with a Static Mean NF/sub min/ of 0.89 dB and a Standard Deviation of 0.07 dB at 4 GHz (1979 [MWSYM])

T. Suzuki, A. Nara, M. Nakatani, T. Ishii, S. Mitsui and K. Shirahata. "Highly Reliable GaAs MESFETs with a Static Mean NF/sub min/ of 0.89 dB and a Standard Deviation of 0.07 dB at 4 GHz (1979 [MWSYM])." 1979 MTT-S International Microwave Symposium Digest 79.1 (1979 [MWSYM]): 393-395.

Optimization of structure and configuration of GaAs MESFETs for high performance and high reliability was investigated. GaAs MESFETs with the NF/sub min/ of 0.89 dB and the standard deviation of 0.07 dB at 4 GHz, the CW and pulse input power capability more than 0.4 W and 2 W, respectively and the failure rate less than 180 Fit have become practical.

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